

This listing of claims will replace all prior versions, and listings, of claims in the present application:

LISTING OF CLAIMS:

Claim 1 (Currently Amended) A method of forming a precision element on a semiconductor substrate comprising ~~the steps of:~~

forming a first element in a first region of a semiconductor substrate;

forming a plurality of second elements in a second region of the substrate, the plurality of second elements comprising individual elements, the individual elements ranging in value about a desired value;

measuring the value of the first element;

comparing the measured value to a target value; and

selecting at least one of the individual second elements corresponding to the result of the comparison to provide a precision element that has said target value using said desired value of said at least one of said selected elements as an offset.

Claim 2 (Original) The method of Claim 1 wherein the plurality of second elements comprise one element having a nominal value about equal to the desired value, another element having a value of about 10 % less than the desired value, and a further element having a nominal value of about 10 % greater than the value of the desired element.

Claim 3 (Original) The method of Claim 2 wherein when the measured value of the first element is greater than the target value, the element having a nominal value of about 10 % less than the desired value is selected.

Claim 4 (Original) The method of Claim 2 wherein when the measured value of the first element is less than a predetermined target value, the element having a nominal value of about 10 % greater than the desired value is selected.

Claim 5 (Original) The method of Claim 2 wherein when the measured value of the first element is equal to the predetermined target value, the element having a value about equal to the value is selected.

Claim 6 (Original) The method of Claim 1 wherein the first and the second elements include a passive element selected from the group consisting of a resistor, a capacitor, a diode and a transistor.

Claim 7 (Original) The method of Claim 1 wherein the first and the second elements are resistors.

Claim 8 (Original) The method of Claim 1 wherein said plurality of second elements is arranged in parallel to each other.

Claim 9 (Original) The method of Claim 1 wherein said plurality of second elements comprise three resistors that are arranged in parallel to each other.

Claim 10 (Original) The method of Claim 1 wherein said plurality of second element is linked by fusible links or antifuses.

Claim 11 (Original) The method of Claim 1 wherein said comparing is performed manually or electronically.

Claim 12 (Original) The method of Claim 1 wherein the selecting includes a step of removing other second elements that are not selected by blowing fusible links or by fusing antifuses that are present within said plurality of second elements.

Claims 13-18 (Cancelled)

Claim 19 (New) A method of forming a precision element on a semiconductor substrate comprising:

forming a first element in a first region of a semiconductor substrate;

forming a plurality of second elements in a second region of the substrate, the plurality of second elements comprising individual elements, the individual elements ranging in value about a desired value, wherein the plurality of second elements comprise one element having a nominal value about equal to the desired value, another element having a value of about 10 % less than the desired value, and a further element having a nominal value of about 10 % greater than the value of the desired element.

measuring the value of the first element;

comparing the measured value to a target value; and

selecting at least one of the individual second elements corresponding to the result of the comparison

Claim 20 (New) The method of Claim 19 wherein when the measured value of the first element is greater than the target value, the element having a nominal value of about 10 % less than the desired value is selected.

Claim 21 (New) The method of Claim 19 wherein when the measured value of the first element is less than a predetermined target value, the element having a nominal value of about 10 % greater than the desired value is selected.

Claim 22 (New) The method of Claim 19 wherein when the measured value of the first element is equal to the predetermined target value, the element having a value about equal to the value is selected.